

# DATA SHEET



## **BST39; BST40** NPN high-voltage transistors

Product specification  
Supersedes data of 2000 Jul 03

2004 Dec 14

# NPN high-voltage transistors

# BST39; BST40

### FEATURES

- Low current (max. 100 mA)
- High voltage (max. 350 V).

### APPLICATIONS

- General purpose switching and amplification.

### DESCRIPTION

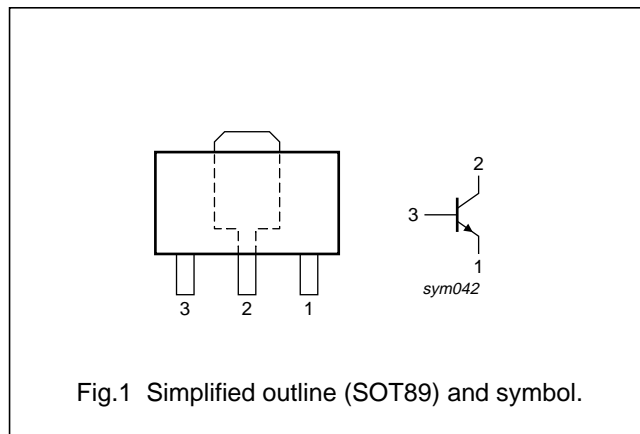
NPN high-voltage transistor in a SOT89 plastic package.  
 PNP complements: BST15 and BST16.

### MARKING

TYPE NUMBER	MARKING CODE
BST39	AT1
BST40	AT2

### PINNING

PIN	DESCRIPTION
1	emitter
2	collector
3	base



### ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
BST39	SC-62	plastic surface mounted package; collector pad for good heat transfer; 3 leads	SOT89
BST40			

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**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter	–	400	V
	BST39			300	V
V <sub>CEO</sub>	collector-emitter voltage	open base	–	350	V
	BST39			250	V
V <sub>EBO</sub>	emitter-base voltage	open collector	–	5	V
I <sub>C</sub>	collector current (DC)		–	100	mA
I <sub>CM</sub>	peak collector current		–	200	mA
I <sub>BM</sub>	peak base current		–	100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	–	1.3	W
T <sub>stg</sub>	storage temperature		–65	+150	°C
T <sub>j</sub>	junction temperature		–	150	°C
T <sub>amb</sub>	ambient temperature		–65	+150	°C

**Note**

- Device mounted on a printed-circuit board, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.  
For other mounting conditions, see *“Thermal considerations for SOT89 in the General Part of associated Handbook”*.

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	note 1	96	K/W
R <sub>th(j-s)</sub>	thermal resistance from junction to soldering point		16	K/W

**Note**

- Device mounted on a printed-circuit board, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.  
For other mounting conditions, see *“Thermal considerations for SOT89 in the General Part of associated Handbook”*.

**CHARACTERISTICS**

T<sub>amb</sub> = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I <sub>CBO</sub>	collector-base cut-off current	I <sub>E</sub> = 0 A; V <sub>CB</sub> = 300 V	–	20	nA
I <sub>EBO</sub>	emitter-base cut-off current	I <sub>C</sub> = 0 A; V <sub>EB</sub> = 5 V	–	100	nA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> = 20 mA; V <sub>CE</sub> = 10 V	40	–	
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = 50 mA; I <sub>B</sub> = 4 mA	–	500	mV
C <sub>c</sub>	collector capacitance	I <sub>E</sub> = i <sub>e</sub> = 0 A; V <sub>CB</sub> = 10 V; f = 1 MHz	–	2	pF
f <sub>T</sub>	transition frequency	I <sub>C</sub> = 10 mA; V <sub>CE</sub> = 10 V; f = 100 MHz	70	–	MHz

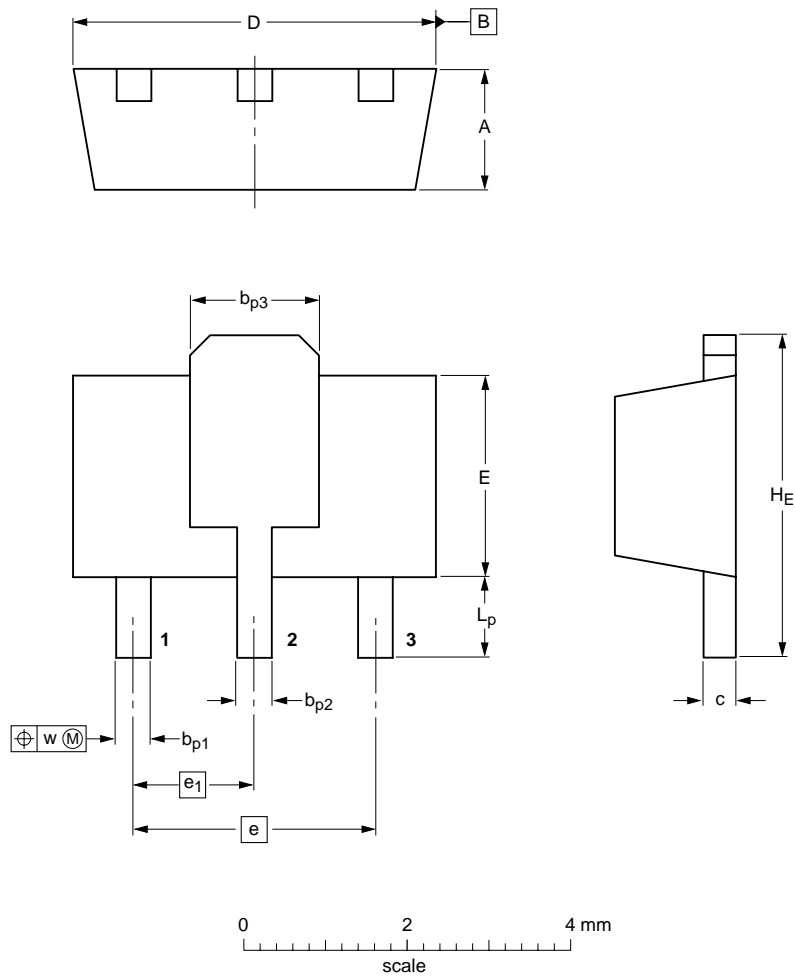
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PACKAGE OUTLINE

Plastic surface mounted package; collector pad for good heat transfer; 3 leads

SOT89



DIMENSIONS (mm are the original dimensions)

UNIT	A	bp1	bp2	bp3	c	D	E	e	e1	HE	Lp	w
mm	1.6 1.4	0.48 0.35	0.53 0.40	1.8 1.4	0.44 0.23	4.6 4.4	2.6 2.4	3.0	1.5	4.25 3.75	1.2 0.8	0.13

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
SOT89		TO-243	SC-62		99-09-13 04-08-03

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## DATA SHEET STATUS

LEVEL	DATA SHEET STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)(3)</sup>	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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